

Appl. No. 10/820,856
Amendment dated: February 16, 2007
Reply to OA of: November 16, 2006

This listing of claims will replace all prior versions and listings of claims in the application.

Listing of Claims:

1 (currently amended). An under bump metallization structure applicable to be disposed on bonding pads of a semiconductor wafer, wherein a passivation layer covers the wafer and exposes the bonding pads, the under bump metallization structure comprising:

- an adhesive layer formed on the bonding pads;
- a first barrier layer disposed on the adhesive layer;
- a wetting layer formed on the first barrier layer; and
- a second barrier layer disposed on the wetting layer, wherein a material of the second barrier comprises tin and copper and wherein the quantity of copper is larger than that of tin.

Claim 2 (canceled).

3 (original). The structure of claim 1, wherein the first barrier layer is a nickel-vanadium layer.

4 (original). The structure of claim 1, wherein the wetting layer is a copper layer.

Claims 5 and 6 (canceled).

7 (original). The structure of claim 1, wherein the thickness of the second barrier layer is ranged from about 50 μm to about 80 μm .

Claims 8-19 (canceled).